## NSN 5961-01-177-4018

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Inclosure Material:
Metal all transistor
Overall Length:
1.062 inches all transistor and 1.245 inches all transistor
Mounting Facility Quantity:
1 all transistor
Internal Configuration:
Junction contact all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
4 transistor
Mounting Method:
Threaded stud all transistor
Features Provided:
Burn in
Overall Width Across Flats:
0.667 inches all transistor and 0.687 inches all transistor
Thread Size:
0.250 inches all transistor
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
400.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter all transistor and 350.0 breakdown voltage,
collector-to-emitter, base open all transistor and 20.0 breakdown voltage, emitter-to-base, collector open all transistor
Current Rating Per Characteristic:
10.00 amperes source cutoff current all transistor
Power Rating Per Characteristic:
75.0 watts small-signal input power, common-collector preset all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction all transistor
Thread Series Designator:
Unf all transistor
Terminal Type And Quantity:
3 tab, solder lug all transistor
Shelf Life:
N/a
Unit Of Measure:
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Demilitarization:

Yes - demil/mli

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